

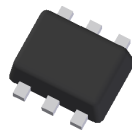
## Features

- $V_{CE0} = -40V$
- $I_C = -200mA$
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Ultra Small Package**

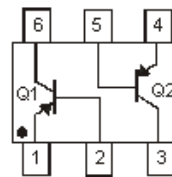
## Mechanical Data

- Case: SOT963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0027 grams (Approximate)

SOT963



Top View



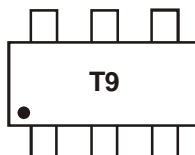
Device Schematic

## Ordering Information (Note 4)

Part Number	Packaging	Shipping
DST3906DJ-7	SOT963	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



T9 = Product Type Marking Code

### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current - Continuous (Note 5)	I <sub>C</sub>	-200	mA

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout.  
 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

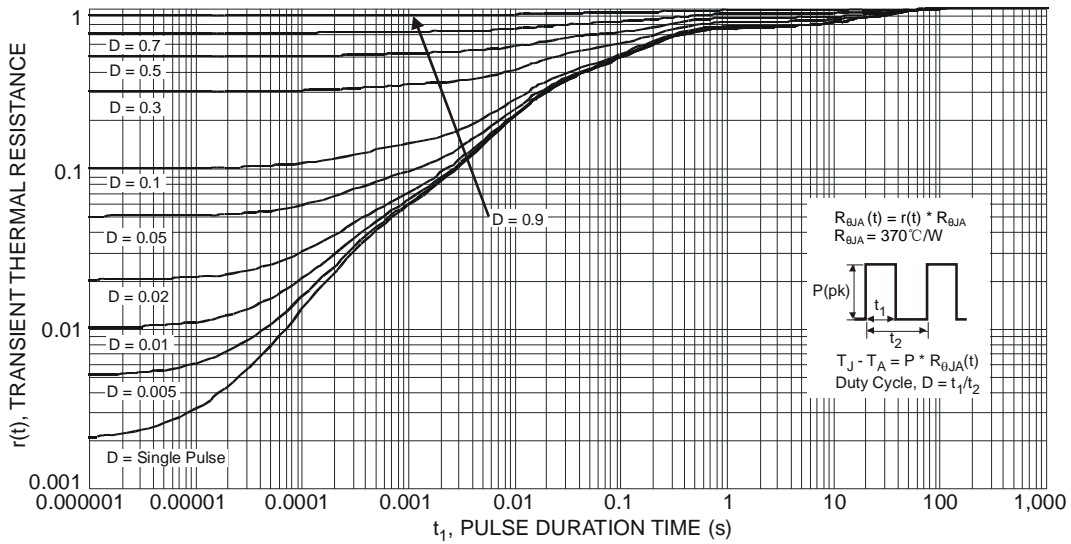


Fig. 1 Transient Thermal Response

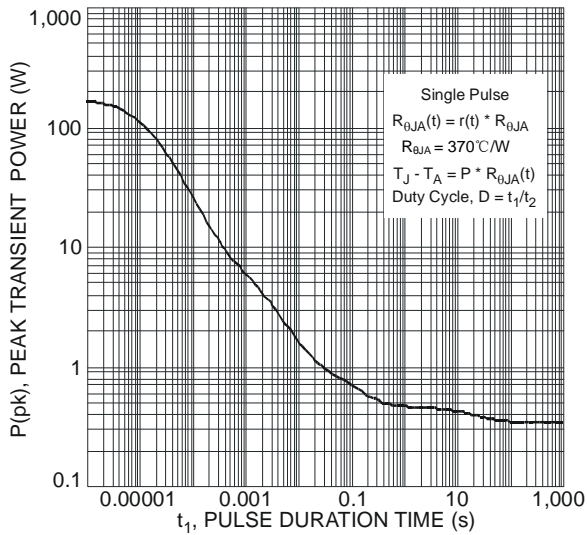


Fig. 2 Single Pulse Maximum Power Dissipation

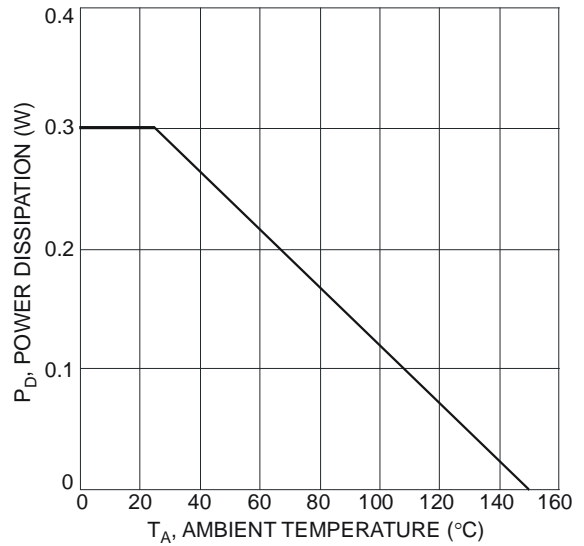


Fig. 3 Power Dissipation vs. Ambient Temperature

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	$V_{(BR)CEO}$	-40	—	V	$I_C = -1\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CEX}$	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3\text{V}$
	$I_{CBO}$	—	-50	nA	$V_{CB} = -30\text{V}, I_E = 0$
Base Cutoff Current	$I_{BL}$	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>					
DC Current Gain	$h_{FE}$	60 80 100 60 30	— — 300 — —	—	$I_C = -100\mu\text{A}, V_{CE} = -1\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -1\text{V}$ $I_C = -10\text{mA}, V_{CE} = -1\text{V}$ $I_C = -50\text{mA}, V_{CE} = -1\text{V}$ $I_C = -100\text{mA}, V_{CE} = -1\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25 -0.40	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65 —	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	$C_{OBO}$	—	4.5	pF	$V_{CB} = -5\text{V}, f = 1\text{MHz}, I_E = 0$
Input Capacitance	$C_{IBO}$	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1\text{MHz}, I_C = 0$
Input Impedance	$h_{ie}$	2	12	$k\Omega$	$V_{CE} = -10\text{V}, I_C = -1\text{mA},$ $f = 1\text{kHz}$
Voltage Feedback Ratio	$h_{re}$	0.1	10	$\times 10^{-4}$	
Small Signal Current Gain	$h_{fe}$	100	400	—	
Output Admittance	$h_{oe}$	3	60	$\mu\text{S}$	
Current Gain-Bandwidth Product	$f_T$	300	—	MHz	
					$V_{CE} = -20\text{V}, I_C = -10\text{mA},$ $f = 100\text{MHz}$
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	$t_D$	—	35	ns	$V_{CC} = -3\text{V}, I_C = -10\text{mA},$
Rise Time	$t_R$	—	35	ns	$I_{B1} = -1\text{mA}$
Storage Time	$t_S$	—	225	ns	$V_{CC} = -3\text{V}, I_C = -10\text{mA},$
Fall Time	$t_F$	—	75	ns	$I_{B2} = 1\text{mA}$

Note: 7. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

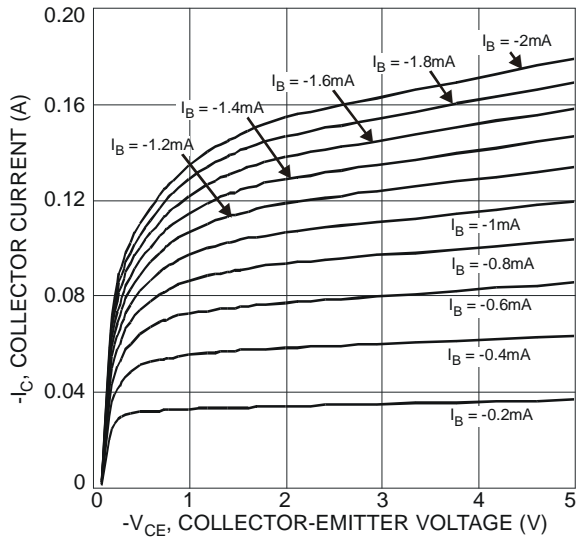


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

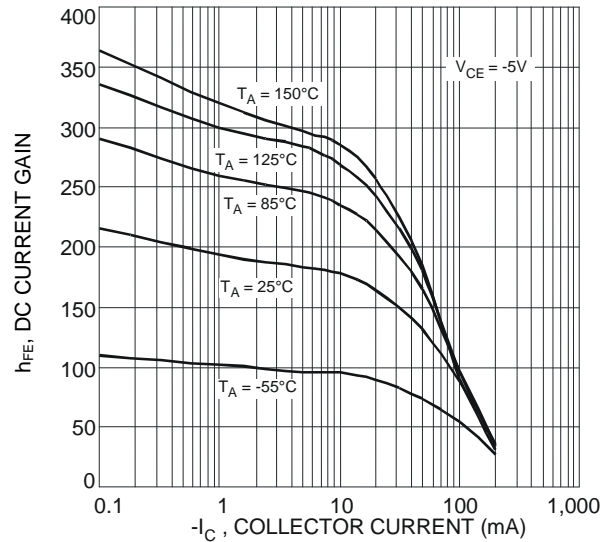


Fig. 5 Typical DC Current Gain vs. Collector Current

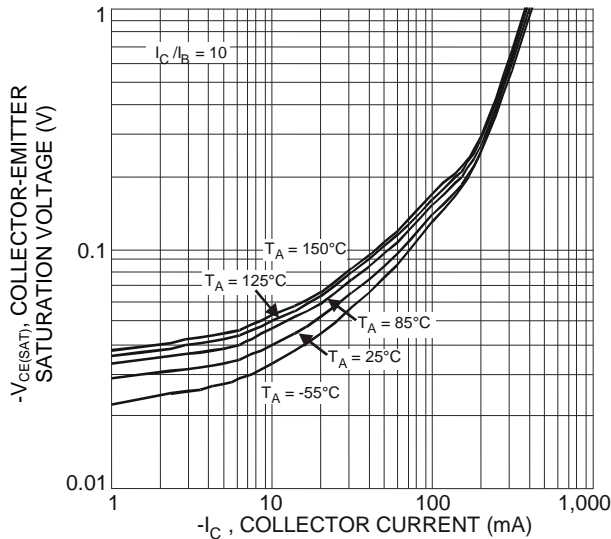


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

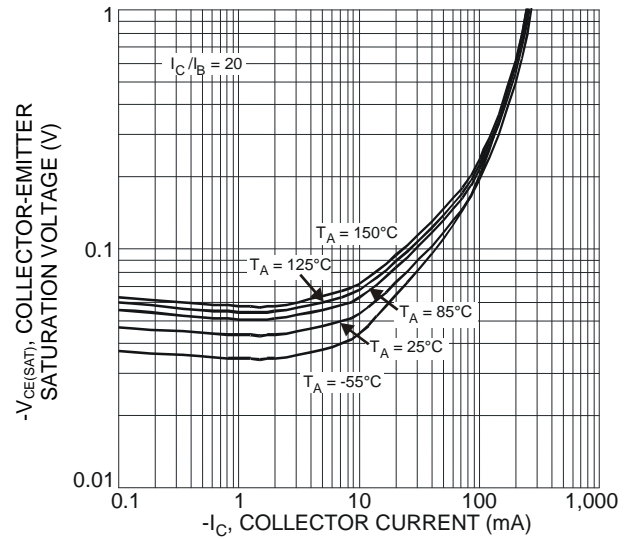


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

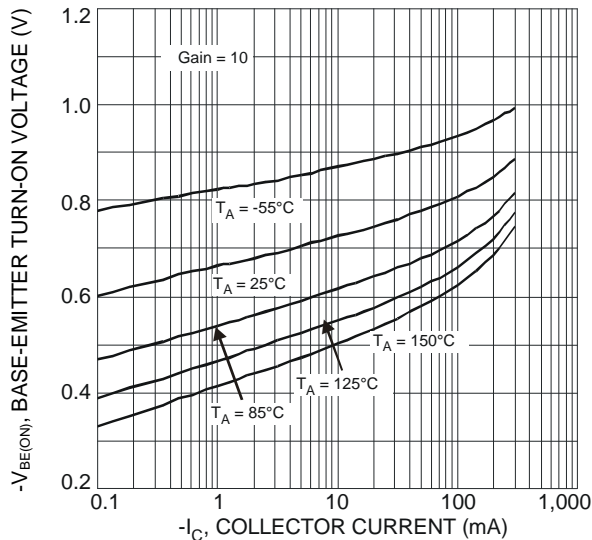


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

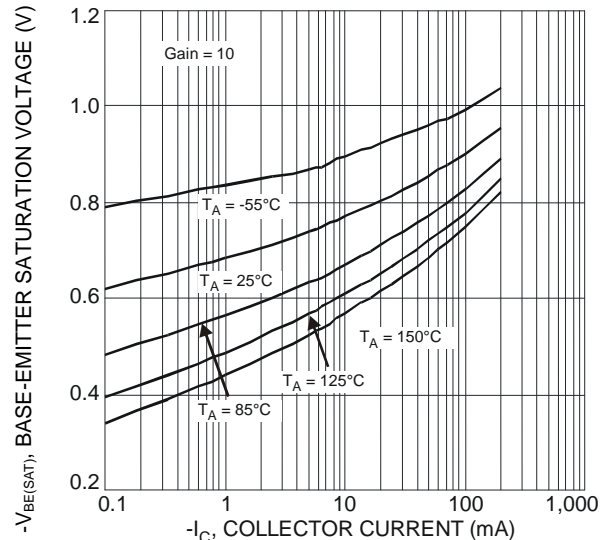
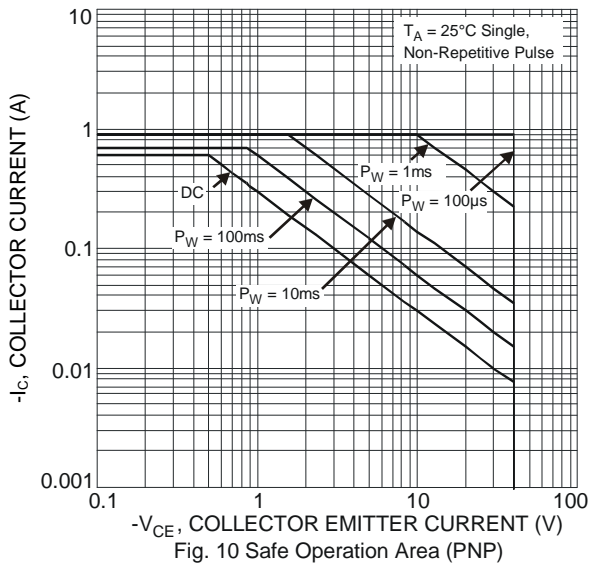


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

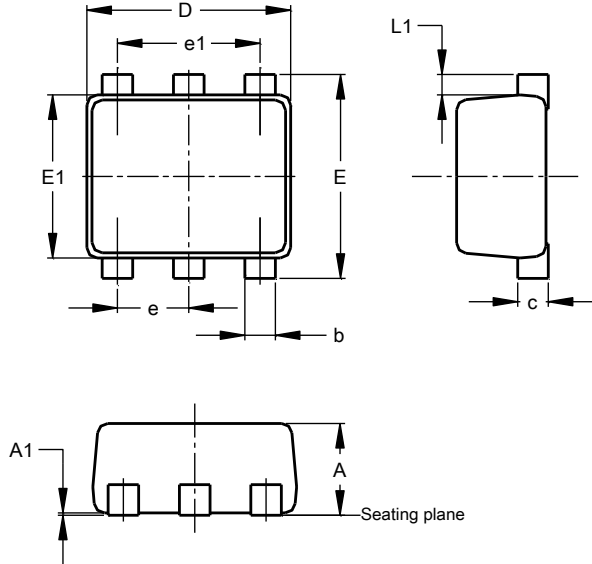
**Typical Electrical Characteristics** (Cont. @ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT963**

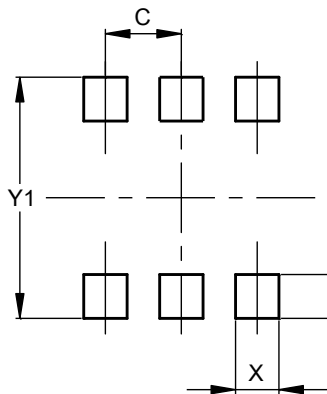


SOT963			
Dim	Min	Max	Typ
A	0.40	0.50	0.45
A1	0.00	0.05	--
b	0.10	0.20	0.15
c	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
e	--	--	0.35
e1	--	--	0.70
L1	0.05	0.15	0.10
All Dimensions in mm			

**Suggest Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT963**



Dimensions	Value (in mm)
C	0.350
X	0.200
Y	0.200
Y1	1.100

Note:

The suggested land pattern dimensions have been provided for reference only, as actual pad layouts may vary depending on application. These dimensions may be modified based on user equipment capability or fabrication criteria. A more robust pattern may be desired for wave soldering and is calculated by adding 0.2mm to the 'Z' dimension. For further information, please reference document IPC-7351A, Naming Convention for Standard SMT Land Patterns, and for International grid details, please see document IEC, Publication 97.

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